

# DATA SHEET

## **PDTC124X series**

NPN resistor-equipped transistors;

R1 = 22 k $\Omega$ , R2 = 47 k $\Omega$

Product specification  
Supersedes data of 1999 May 18

2003 Apr 10

## NPN resistor-equipped transistors; R1 = 22 k $\Omega$ , R2 = 47 k $\Omega$

## PDTC124X series

### FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

### APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

### QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	–	50	V
I <sub>O</sub>	output current (DC)	–	100	mA
R1	bias resistor	22	–	k $\Omega$
R2	bias resistor	47	–	k $\Omega$

### DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

### PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT
	PHILIPS	EIAJ		
PDTC124XE	SOT416	SC-75	32	PDTA124XE
PDTC124XEF	SOT490	SC-89	32	PDTA124XEF
PDTC124XK	SOT346	SC-59	51	PDTA124XK
PDTC124XM	SOT883	SC-101	DZ	PDTA124XM
PDTC124XS	SOT54 (TO-92)	SC-43	TC124X	PDTA124XS
PDTC124XT	SOT23	–	*46 <sup>(1)</sup>	PDTA124XT
PDTC124XU	SOT323	SC-70	*51 <sup>(1)</sup>	PDTA124XU

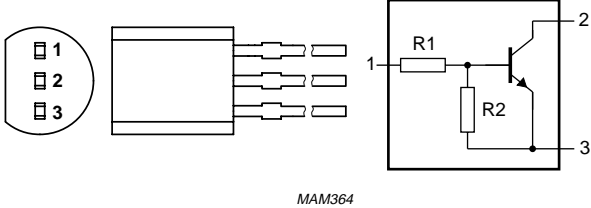
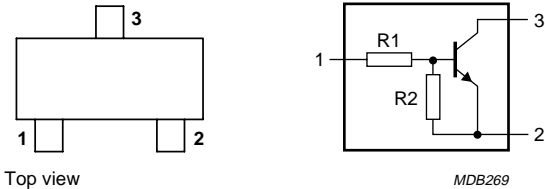
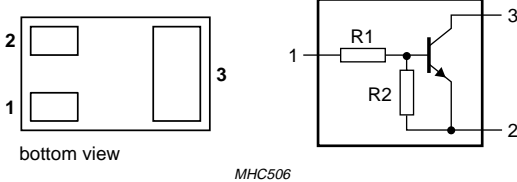
### Note

- \* = p: Made in Hong Kong.  
\* = t: Made in Malaysia.  
\* = W: Made in China.

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PDTC124X series

SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC124XS	 <i>MAM364</i>	1 2 3	base collector emitter
PDTC124XE PDTC124XEF PDTC124XK PDTC124XT PDTC124XU	 Top view <i>MDB269</i>	1 2 3	base emitter collector
PDTC124XM	 bottom view <i>MHC506</i>	1 2 3	base emitter collector

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### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	–	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	–	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	–	10	V
V <sub>I</sub>	input voltage				
	positive		–	+40	V
	negative		–	–7	V
I <sub>O</sub>	output current (DC)		–	100	mA
I <sub>CM</sub>	peak collector current		–	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT54	note 1	–	500	mW
	SOT23	note 1	–	250	mW
	SOT346	note 1	–	250	mW
	SOT323	note 1	–	200	mW
	SOT416	note 1	–	150	mW
	SOT490	notes 1 and 2	–	250	mW
	SOT883	notes 2 and 3	–	250	mW
T <sub>stg</sub>	storage temperature		–65	+150	°C
T <sub>j</sub>	junction temperature		–	150	°C
T <sub>amb</sub>	operating ambient temperature		–65	+150	°C

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air		
	SOT54	note 1	250	K/W
	SOT23	note 1	500	K/W
	SOT346	note 1	500	K/W
	SOT323	note 1	625	K/W
	SOT416	note 1	833	K/W
	SOT490	notes 1 and 2	500	K/W
	SOT883	notes 2 and 3	500	K/W

### Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60  $\mu$ m copper strip line.

NPN resistor-equipped transistors;  
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## PDTC124X series

**CHARACTERISTICS**

T<sub>amb</sub> = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0	–	–	100	nA
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0	–	–	1	$\mu$ A
		V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0; T <sub>j</sub> = 150 °C	–	–	50	$\mu$ A
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0	–	–	120	$\mu$ A
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 5 mA	80	–	–	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.5 mA	–	–	150	mV
V <sub>i(off)</sub>	input-off voltage	I <sub>C</sub> = 100 $\mu$ A; V <sub>CE</sub> = 5 V	–	0.8	0.5	V
V <sub>i(on)</sub>	input-on voltage	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 0.3 V	2	1.1	–	V
R1	input resistor		15.4	22	28.6	k $\Omega$
$\frac{R2}{R1}$	resistor ratio		1.7	2.1	2.6	
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	–	–	2.5	pF

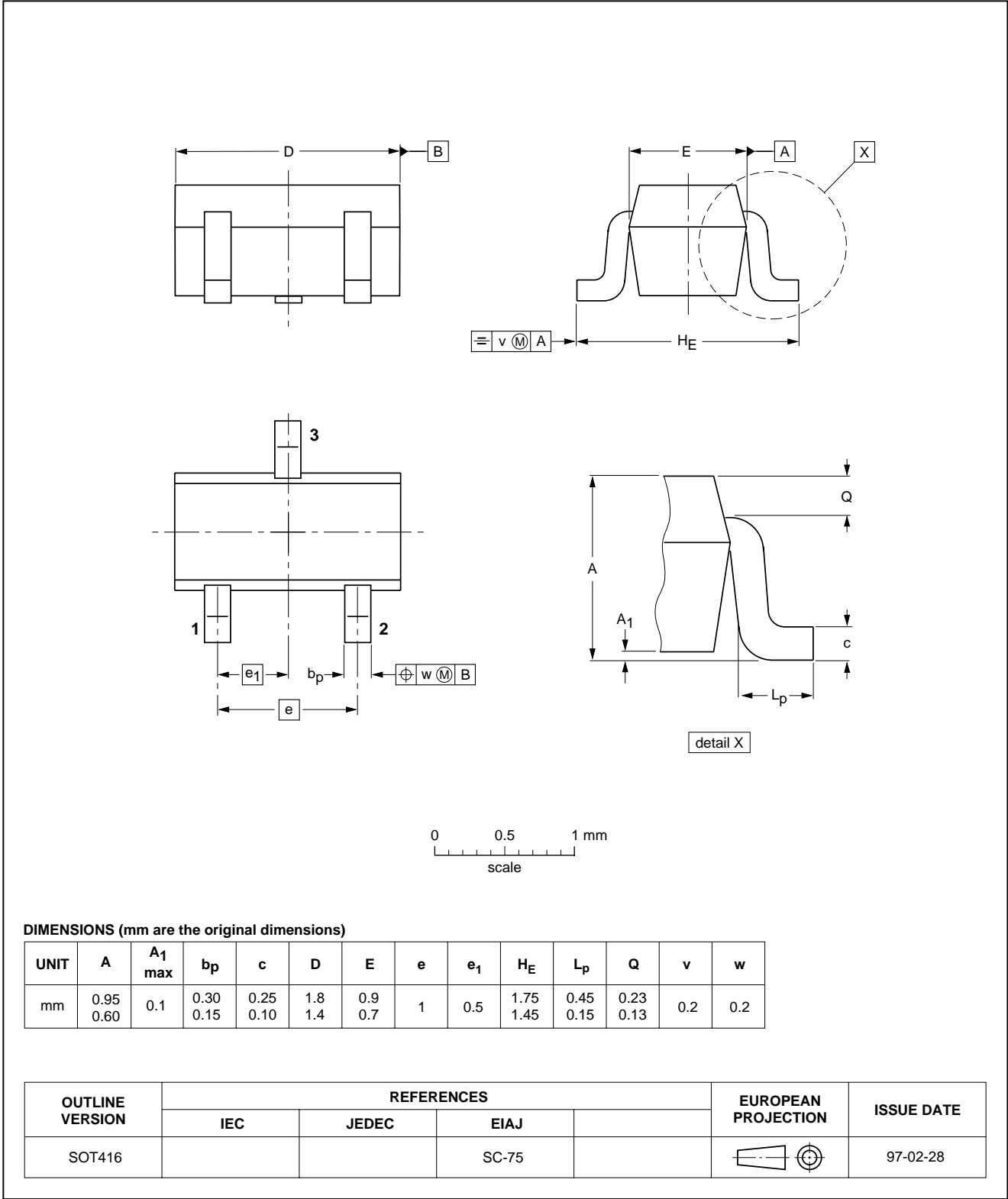
NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 47 kΩ

PDTC124X series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT416

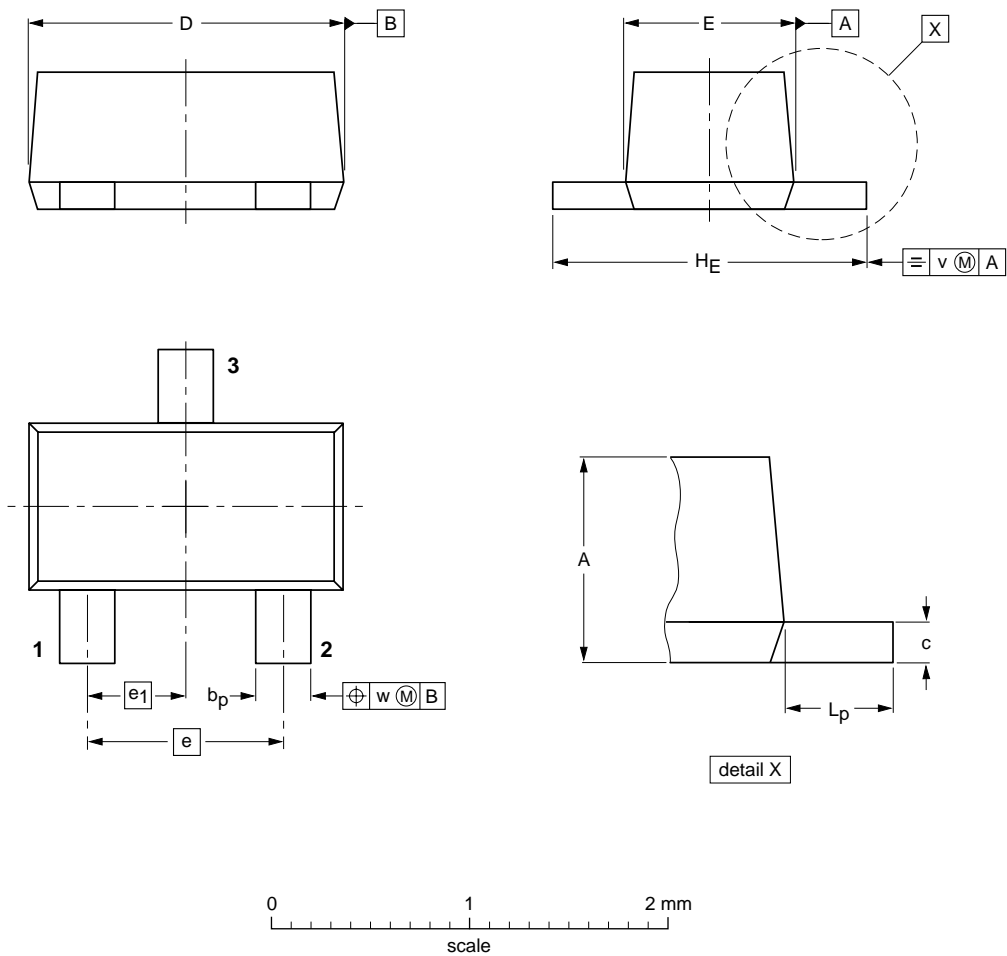


NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 47 kΩ

PDTC124X series

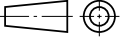
Plastic surface mounted package; 3 leads

SOT490



DIMENSIONS (mm are the original dimensions)

UNIT	A	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

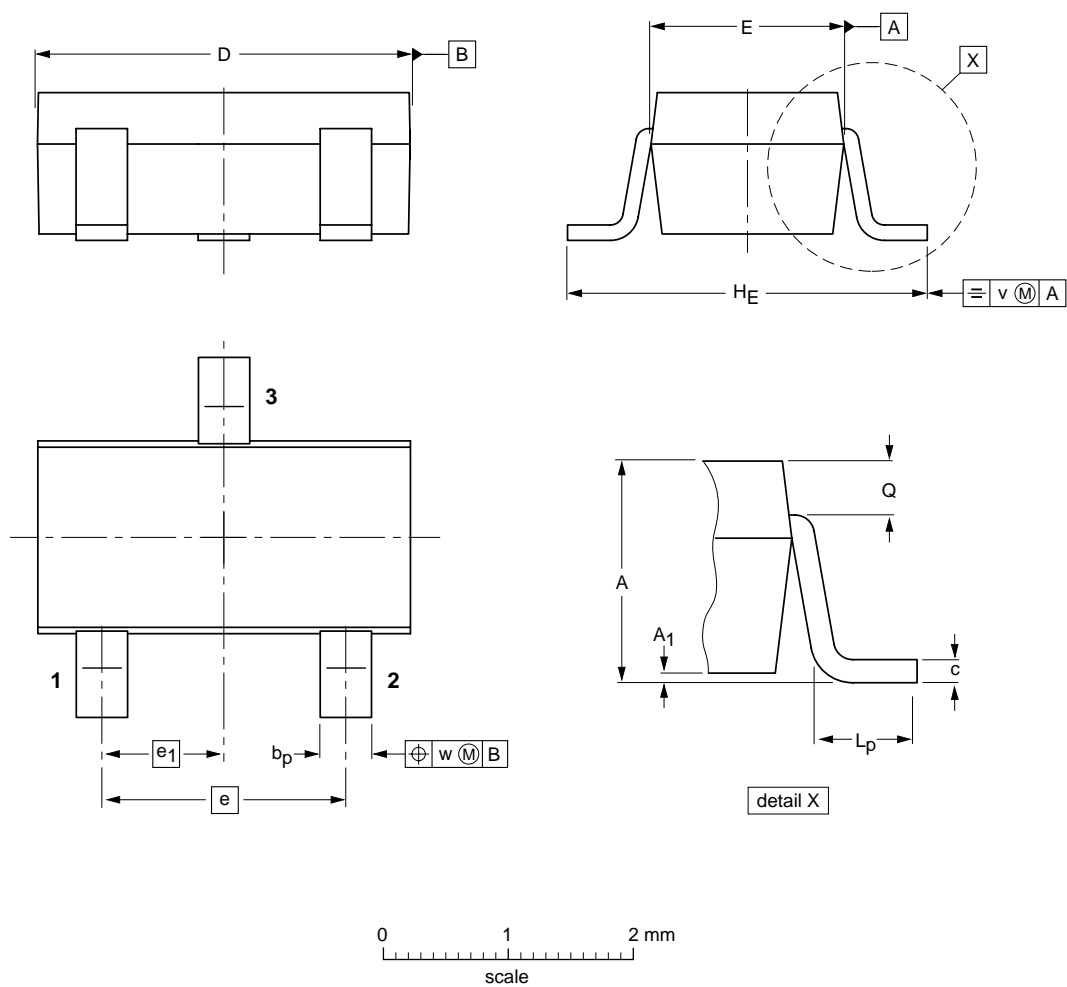
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT490			SC-89			98-10-23

NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 47 kΩ

PDTC124X series

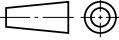
Plastic surface mounted package; 3 leads

SOT346



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.3 1.0	0.1 0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

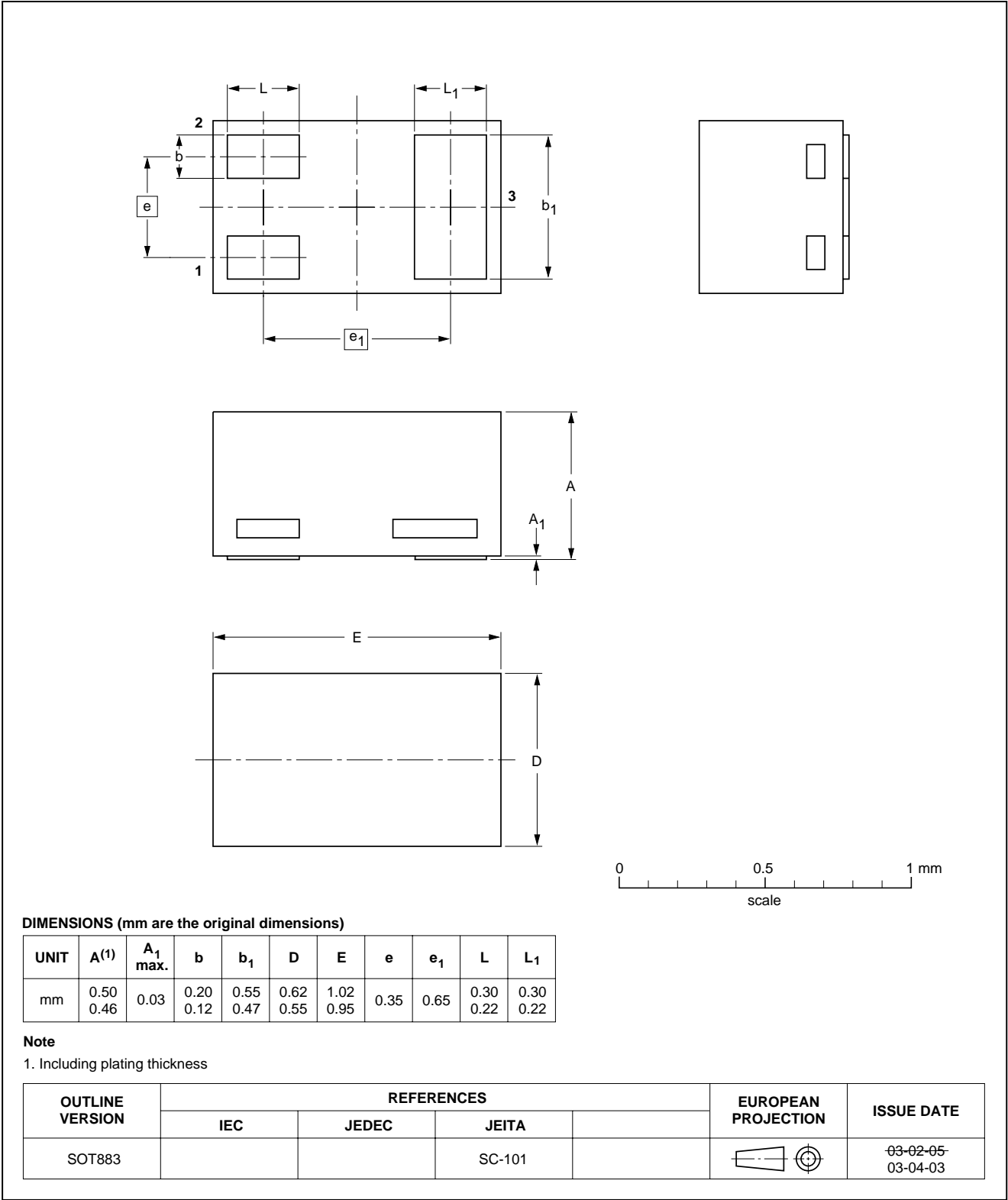


NPN resistor-equipped transistors;  
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PDTC124X series

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

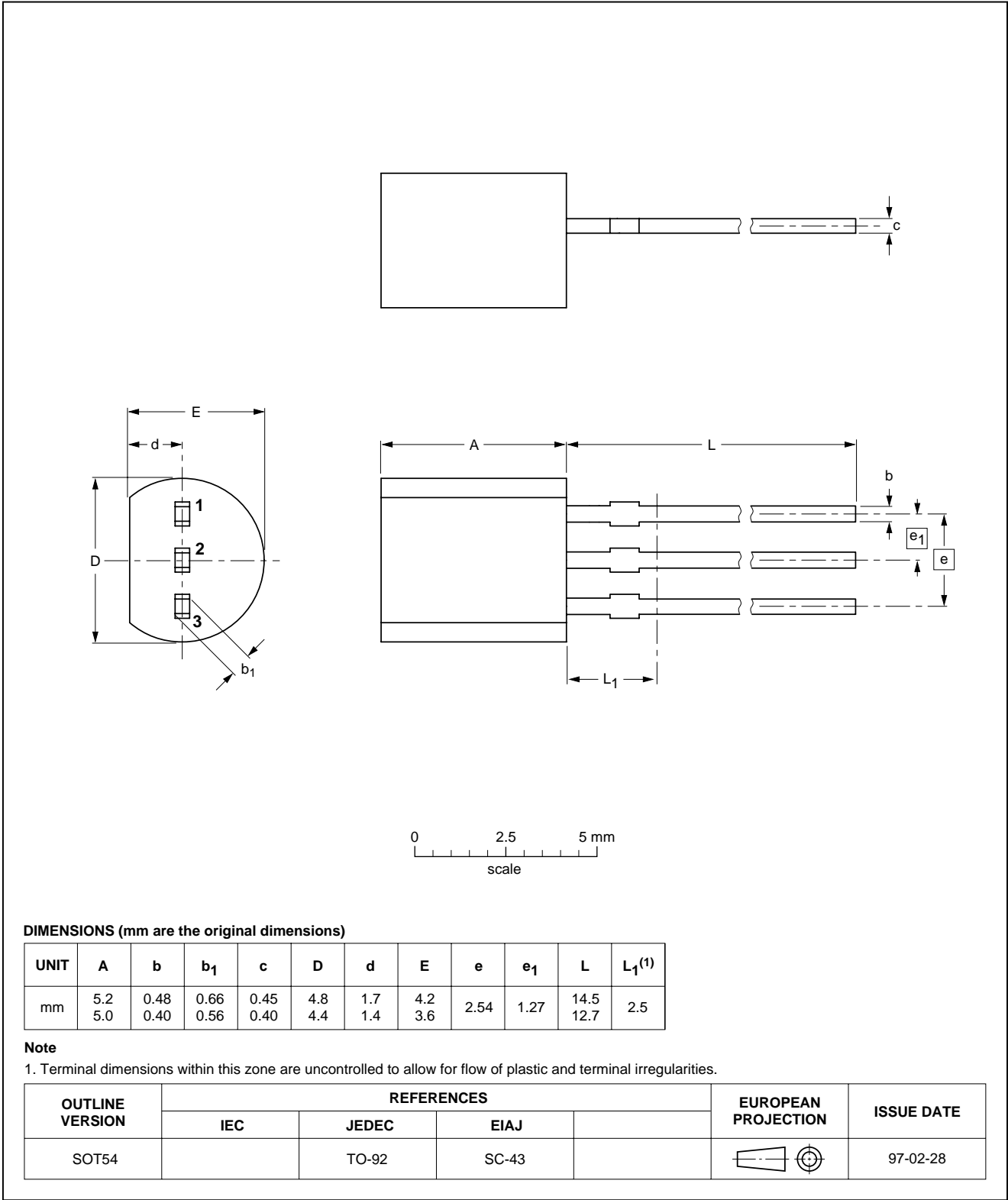


NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 47 kΩ

PDTC124X series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

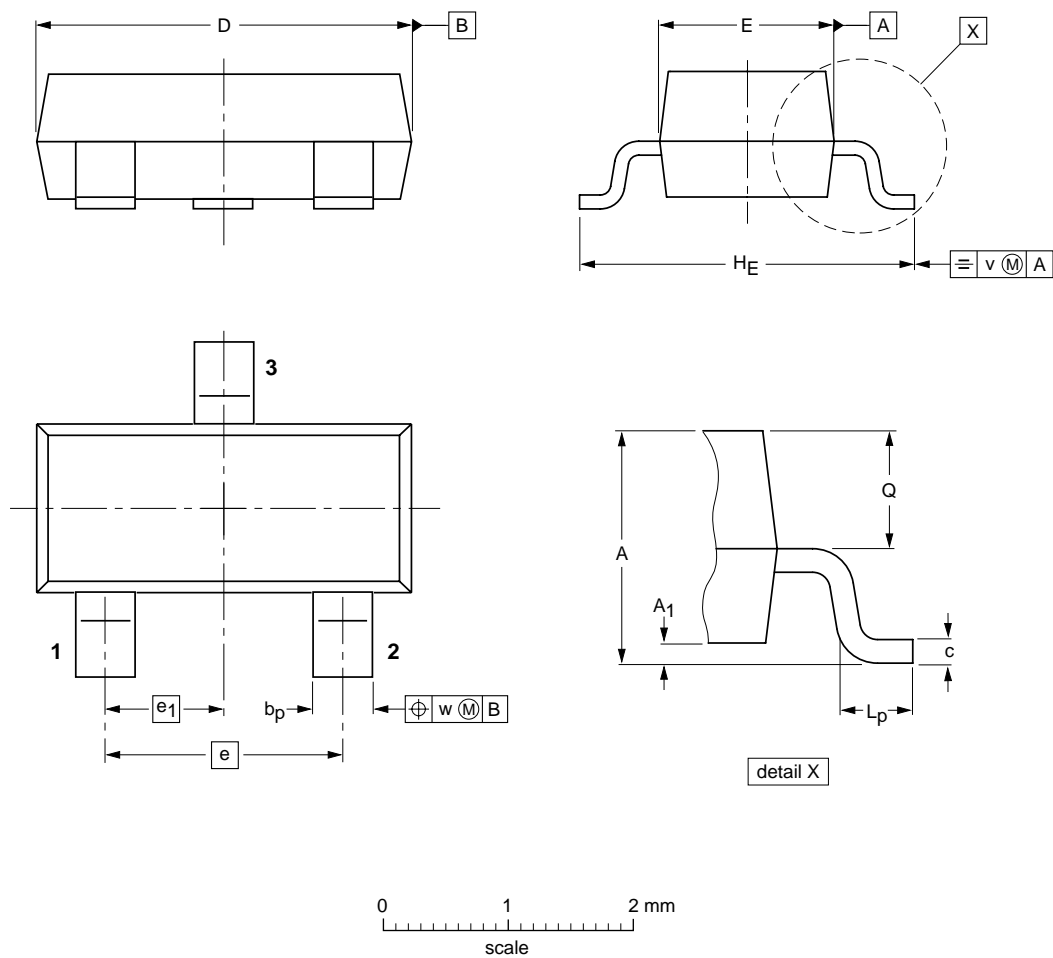


NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 47 kΩ

PDTC124X series

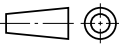
Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max.	b <sub>P</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>P</sub>	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

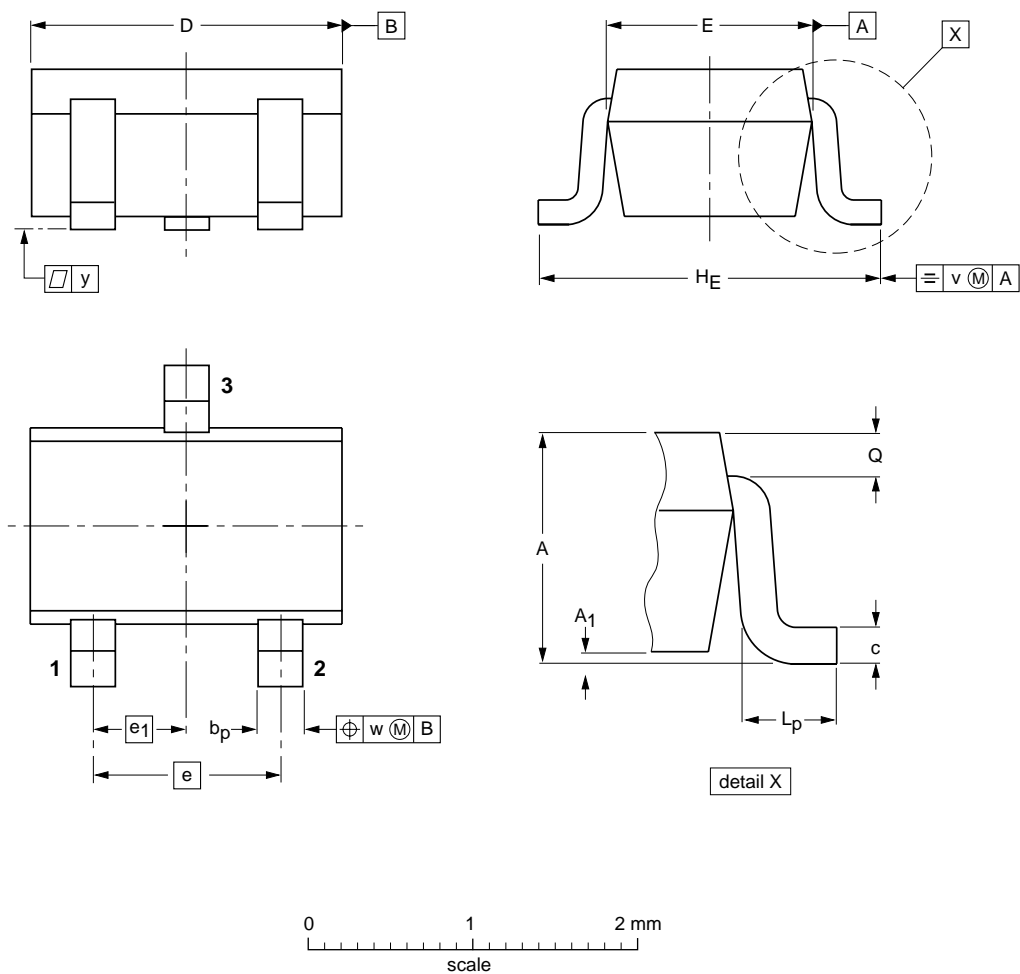
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

NPN resistor-equipped transistors;  
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PDTC124X series


Plastic surface mounted package; 3 leads

SOT323



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub> max	b <sub>p</sub>	c	D	E	e	e <sub>1</sub>	H <sub>E</sub>	L <sub>p</sub>	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN resistor-equipped transistors;  
R1 = 22 kΩ, R2 = 47 kΩ

PDTC124X series

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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#### NOTES

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PDTC124X series

#### NOTES

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Printed in The Netherlands

613514/04/pp16

Date of release: 2003 Apr 10

Document order number: 9397 750 11018

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